



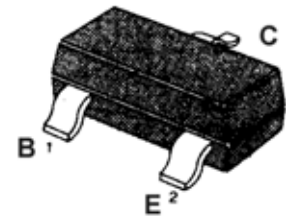
《风光欣》技术资料

2SC3356(R25) NPN EPITAXIAL SILICON TRANSISTOR

ELECTRICAL CHARACTERISTICS (T_A=25)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	20	V
Collector-Emitter Voltage	V _{CE0}	12	V
Emitter -Base Voltage	V _{EBO}	3	V
Collector Current	I _c	100	mA
Collector Dissipation	P _c	200	mW
Junction Temperature	T _J	150	
Storage Temperature	T _{STG}	-65 ~150	

SOT-23



ELECTRICAL CHARACTERISTICS (T_A=25)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _c =100μA, I _E =0	20			V
Collector-Emitter Breakdown Voltage	BV _{CE0}	I _c =2mA, I _B =0	12			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =100μA, I _c =0	3			V
Collector Cut-off Current	I _{CB0}	V _{CB} = 20V, I _E =0			100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 6V, I _E =0			100	nA
DC Current Gain	H _{FE}	V _{CE} = 10V, I _c = 3mA	75	120	300	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = 10mA, I _B = 1mA			0.2	V
Output Capacitance	C _{OB} f=1MHz	V _{CB} = 10V, I _E = 0		0.55		pF
Current Gain-Bandwidth Product	f _T	V _{CB} = 4V, I _c = 5mA		4500	7000	MHz